MBR1060 and MBR10100 are Preferred Devices

# **SWITCHMODE** <sup>™</sup> **Power Rectifiers**

This series of SWITCHMODE power rectifiers uses the Schottky Barrier principle with a platinum barrier metal. These state—of—the—art devices have the following features:

#### **Features**

- Guard–Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Pb-Free Packages are Available\*

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



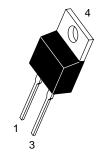
## ON Semiconductor®

http://onsemi.com

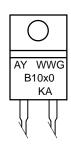
# SCHOTTKY BARRIER RECTIFIERS 10 AMPERES, 60 to 100 VOLTS



#### MARKING DIAGRAM



TO-220AC CASE 221B PLASTIC



A = Assembly Location

Y = Year

WW = Work Week

G = Pb-Free Package

B10x0 = Device Code

x = 6, 8, 9 or 10

KA = Diode Polarity

#### **ORDERING INFORMATION**

Device	Package	Shipping
MBR1060	TO-220	50 Units/Rail
MBR1060G	TO-220 (Pb-Free)	50 Units/Rail
MBR1080	TO-220	50 Units/Rail
MBR1080G	TO-220 (Pb-Free)	50 Units/Rail
MBR1090	TO-220	50 Units/Rail
MBR1090G	TO-220 (Pb-Free)	50 Units/Rail
MBR10100	TO-220	50 Units/Rail
MBR10100G	TO-220 (Pb-Free)	50 Units/Rail

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **MAXIMUM RATINGS**

Rating		MBR				
		1060	1080	1090	10100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	80	90	100	V
Average Rectified Forward Current (Rated V <sub>R</sub> ) T <sub>C</sub> = 133°C	I <sub>F(AV)</sub>	10		Α		
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz) T <sub>C</sub> = 133°C	I <sub>FRM</sub>	20		А		
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I <sub>FSM</sub>	150		А		
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	0.5		Α		
Operating Junction Temperature (Note 1)	TJ	- 65 to +175		°C		
Storage Temperature	T <sub>stg</sub>	- 65 to +175		°C		
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000		V/μs		

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

#### THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction-to-Case		2.0	°C/W		
Maximum Thermal Resistance, Junction-to-Ambient		60	°C/W		
ELECTRICAL CHARACTERISTICS					
Maximum Instantaneous Forward Voltage (Note 2)	V <sub>F</sub>	0.7	V		
$(i_F = 10 \text{ Amps}, T_C = 125^{\circ}C)$		0.7			

Maximum mistantaneous i orward voltage (Note 2)	1 VF		v	П
$(i_F = 10 \text{ Amps}, T_C = 125^{\circ}C)$		0.7		
$(i_F = 10 \text{ Amps}, T_C = 25^{\circ}C)$		0.8		
$(i_F = 20 \text{ Amps}, T_C = 125^{\circ}C)$		0.85		
$(i_F = 20 \text{ Amps}, T_C = 25^{\circ}C)$		0.95		
Maximum Instantaneous Reverse Current (Note 2)	i <sub>R</sub>		mA	ł
(Rated dc Voltage, T <sub>C</sub> = 125°C)	''K	6.0	''''	
(Rated dc Voltage, $T_C = 25^{\circ}C$ )		0.10		
(		3.10		ı

<sup>2.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

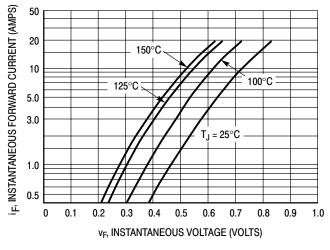
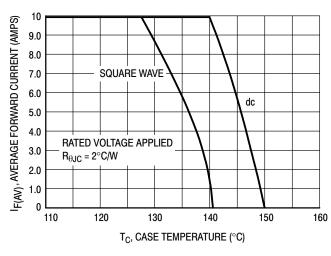


Figure 1. Typical Forward Voltage

**Figure 2. Typical Reverse Current** 



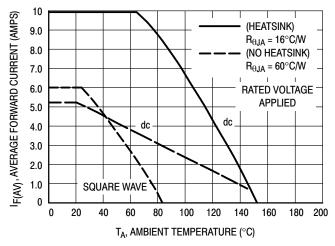


Figure 3. Current Derating, Case

Figure 4. Current Derating, Ambient

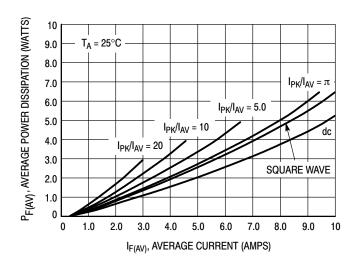
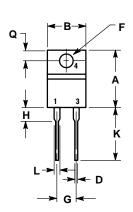
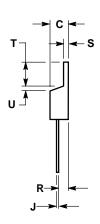


Figure 5. Forward Power Dissipation

#### **PACKAGE DIMENSIONS**

TO-220 PLASTIC CASE 221B-04 ISSUE D





#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

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